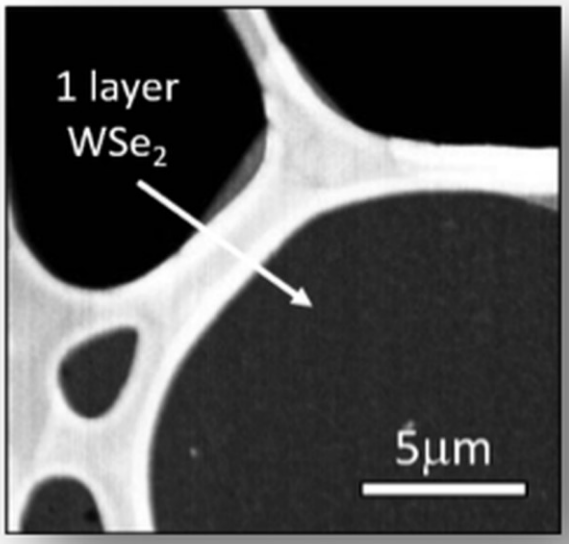
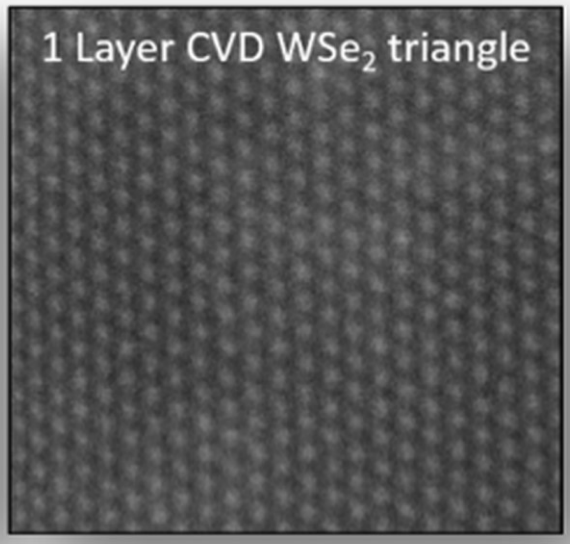
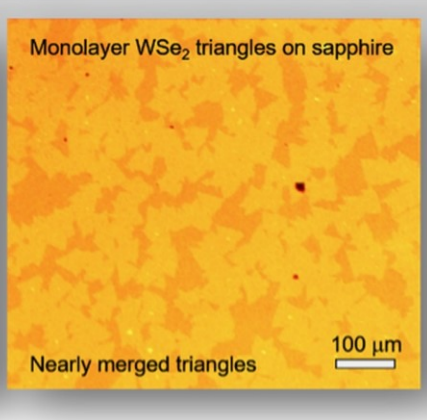
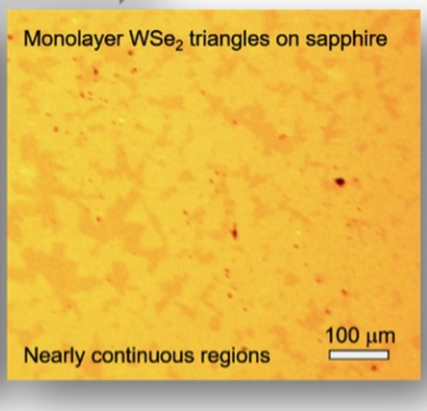
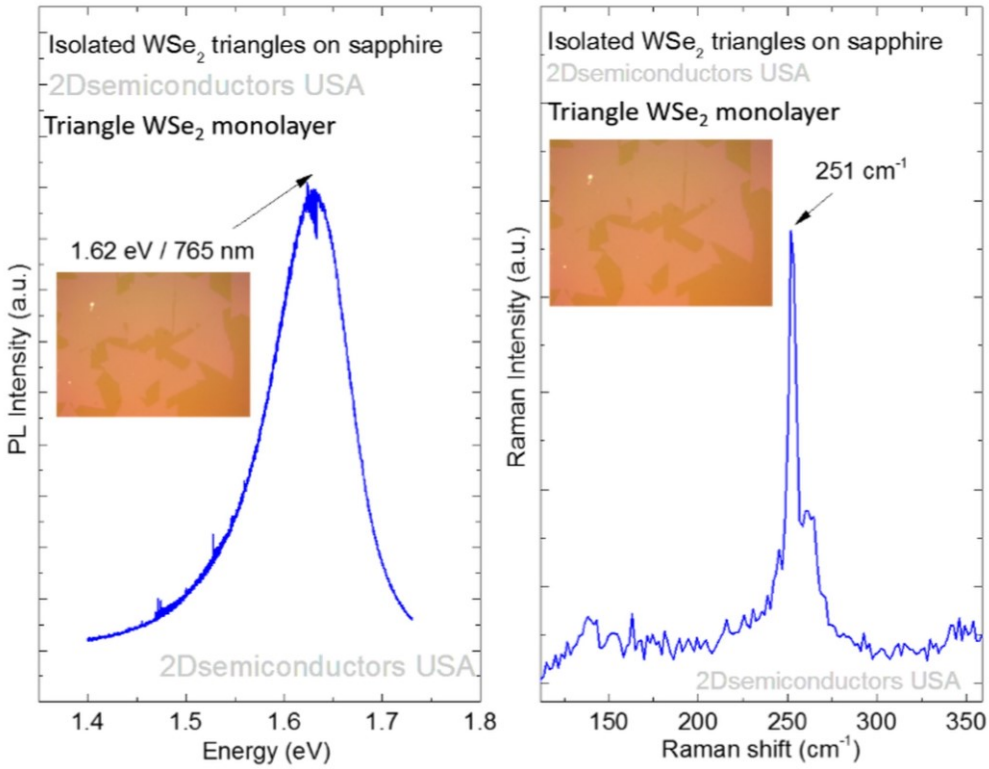




These regions can be observed on the same sample







Sample Properties

Sample size	1cm x 1cm square shaped
Substrate type	(0001) c-cut sapphire
Coverage	Isolated and partially merged monolayer triangles
Electrical properties	1.62 eV Direct Bandgap Semiconductor
Crystal structure	Hexagonal Phase
Unit cell parameters	a = b = 0.327 nm, c = 1.295 nm, α = β = 90°, γ = 120°
Production method	Low pressure Chemical Vapor Deposition (LPCVD)
Characterization methods	Raman, photoluminescence, TEM, EDS